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making a nitrogen concentration of part of the gate insulating film except under the gate electrodes lower than a nitrogen concentration of part of the gate insulating film which lies under the gate electrodes by oxidizing the gate electrodes and the gate insulating film by at least one of a vaporizer method, an oxyhydrogen combustion method, and a wet oxidation method performed at temperatures not lower than 950°C; and

forming impurity diffused layers on both sides of the respective gate electrodes in the semiconductor substrate.

#### REMARKS

Favorable reconsideration of this application as presently amended and in light of the following discussion is respectfully requested.

Claims 1-4, 7, 10, 12-18, 20 and 22 are pending in the present application. Claim 10 has been amended by the present amendment.

Claim 10 has been amended to include a feature which was inadvertently not included in the previous response. This additional feature is the same feature included in other independent claims such as Claims 1 and 12, for example. It is believed no new matter has been added.

Consequently, an action on the merits is earnestly solicited.

Respectfully submitted,

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IN THE CLAIMS

10. (Twice Amended) A semiconductor device manufacturing method comprising:

forming a gate insulating film in an oxynitride form on a main surface of a semiconductor substrate;

forming gate electrodes on the gate insulating film;

making a nitrogen concentration of part of the gate insulating film except under the gate electrodes lower than a nitrogen concentration of part of the gate insulating film which lies under the gate electrodes by oxidizing the gate electrodes and the gate insulating film by at least one of a vaporizer method, an oxyhydrogen combustion method, and a wet oxidation method performed at temperatures not lower than 950°C; and

forming impurity diffused layers on both sides of the respective gate electrodes in the semiconductor substrate.

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